

PATENT  
81872.0055  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:  
  
Yosuke INOMATA  
  
Serial No: Not assigned  
  
Filed: January 22, 2004  
  
For: Multicrystalline Silicon Substrate and Process for  
Roughening Surface Thereof

Art Unit: Not assigned  
  
Examiner: Not assigned

**TRANSMITTAL OF INFORMATION DISCLOSURE  
STATEMENT**

Mail Stop PATENT APPLICATION  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

The information disclosure statement submitted herewith is being filed concurrently with the subject application [37 C.F.R. § 1.97(b)] and contains no items of information cited in any communication from a foreign patent office in a counterpart foreign application [37 C.F.R. § 1.97(e)(1)].

If it should be determined that for any reason either an insufficient or excessive fee has been paid, please charge any insufficiency or credit any overpayment necessary to ensure consideration of the information disclosure statement for the above-identified application to Deposit Account No. 50-1314. A copy of this paper is enclosed.

Respectfully submitted,

HOGAN & HARTSON L.L.P.

Date: January 22, 2004  
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FORM PTO-1449		Docket Number (Optional) 81872.0055		Application Number Not assigned	
INFORMATION DISCLOSURE CITATION IN AN APPLICATION		Applicant Yosuke INOMATA			
(Use several sheets if necessary)		Filing Date January 22, 2004		Group Art Unit Not assigned	
<b>U.S. PATENT DOCUMENTS</b>					
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
<b>FOREIGN PATENT DOCUMENTS</b>					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS
	09-102625	04/15/97	Japan		Abstract
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>					
<b>EXAMINER</b>	<b>DATE CONSIDERED</b>				